Elektronische Bauelemente

BCW61C

-0.1A , -32V

PNP Plastic Encapsulated Transistor

RoHS Compliant Product

A suffix of "-C" specifies halogen & lead-free

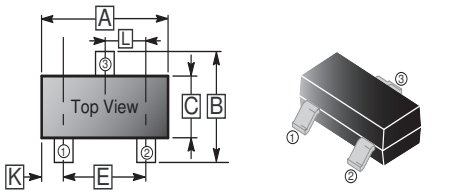
FEATURES

- Low current
- Low voltage

MARKING :

BC

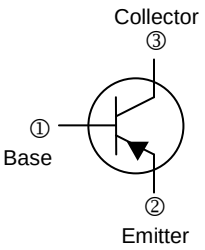
SOT-23



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	2.80	3.04	G	0.09	0.18
B	2.10	2.55	H	0.45	0.60
C	1.20	1.40	J	0.08	0.177
D	0.89	1.15	K	0.6 REF.	
E	1.78	2.04	L	0.89	1.02
F	0.30	0.50			

PACKAGE INFORMATION

Package	MPQ	Leader Size
SOT-23	3K	7 inch



ABSOLUTE MAXIMUM RATINGS (T_A=25°C unless otherwise specified)

Parameter	Symbol	Ratings	Unit
Collector to Base Voltage	V_{CBO}	-32	V
Collector to Emitter Voltage	V_{CEO}	-32	V
Emitter to Base Voltage	V_{EBO}	-5	V
Collector Current - Continuous	I_C	-100	mA
Collector Power Dissipation	P_C	0.25	W
Junction, Storage Temperature	T_J, T_{STG}	150, -55~150	℃

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise specified)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Collector to Base Breakdown Voltage	$V_{(BR)CBO}$	-32	-	-	V	I_C= -10μA, I_E=0
Collector to Emitter Breakdown Voltage	$V_{(BR)CEO}$	-32	-	-	V	I_C= -1mA, I_B=0
Emitter to Base Breakdown Voltage	$V_{(BR)EBO}$	-5	-	-	V	I_E= -10μA, I_C=0
Collector Cut-Off Current	I_{CBO}	-	-	-0.02	μA	V_{CB}=-32V, I_E=0
Emitter Cut-Off Current	I_{EBO}	-	-	-0.02	μA	V_{EB}= -4V, I_C=0
DC Current Gain	$h_{FE\ (1)}$	40	-	-		V_{CE}= -5V, I_C= -10μA
	$h_{FE\ (2)}$	250	-	460		V_{CE}= -5V, I_C= -2mA
	$h_{FE\ (3)}$	100	-	-		V_{CE}= -1V, I_C= -50mA
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	-0.06	-	-0.25	V	I_C= -10mA, I_B= -0.25mA
		-0.12	-	-0.55	V	I_C= -50mA, I_B= -1.25mA
Base to Emitter Saturation Voltage	$V_{BE(sat)}$	-0.6	-	-0.85	V	I_C= -10mA, I_B= -0.25mA
		-0.68	-	-1.05	V	I_C= -50mA, I_B= -1.25mA
Base to Emitter Voltage	V_{BE}	-	-0.55	-	V	V_{CE}= -5V, I_C= -10μA
		-0.6	-	-0.75	V	V_{CE}= -5V, I_C= -2mA
		-	-0.72	-	V	V_{CE}= -1V, I_C= -50mA
Transition Frequency	f_T	100	-	-	MHz	V_{CE}= -5V, I_C= -10mA, f=100MHz
Collector capacitance	C_c	-	4.5	-	pF	V_{CB}= -10V, I_E=0, f=1MHz
Emitter capacitance	C_e	-	11	-	pF	V_{EB}= -0.5V, I_c=0, f=1MHz

CHARACTERISTIC CURVES